SOP-8 .> / / x P ?ú 3 Power Trench MOS « | • ’ož
P-Channel Power Trench MOSFET in a SOP-8 Plastic Package.

z õ â > k • ¼ , † ½ k ä Å ?ú $ Đ â z $R_{DS\ g\ ON\ h}$k ä ä y v Ô ò ½ož —)í D }ož
Low gate charge, Fast switching speed, High performance trench technology for extremely, low $R_{DS(ON)}$, High power and current handling capability. Halogen-free Product.

› ’ ò k ¿ > • ¼ k P ‘ ož
Power management, Load switch, Battery protection.

PIN1o•PIN 2o•PIN 3 y S PIN 4 y G
PIN5o•PIN 6o•PIN 7o•PIN 8 y D

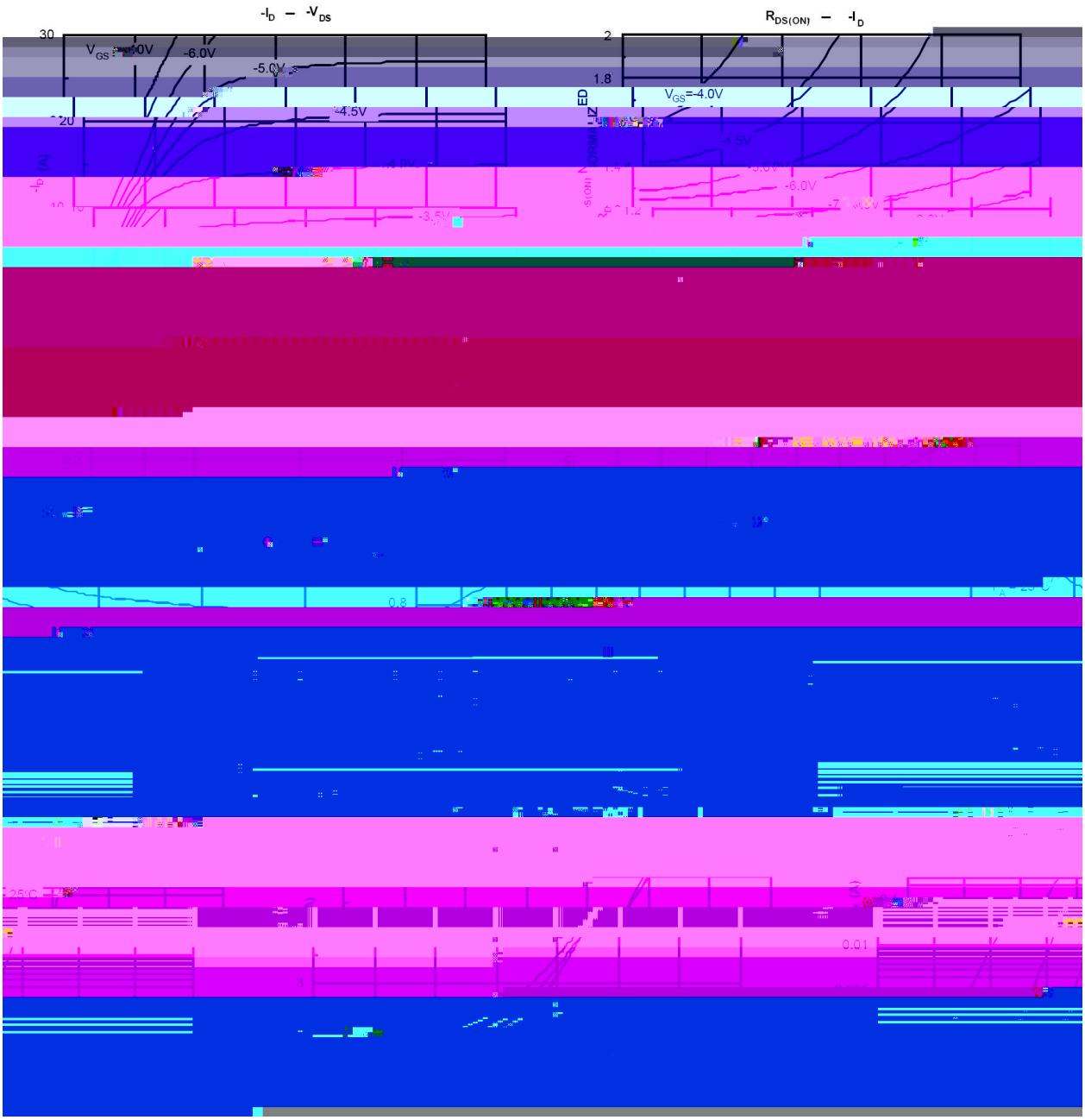
@ *f* Parameter	… Z Symbol	*f* › Rating	% y Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V		

Ô4ì × ? d ;

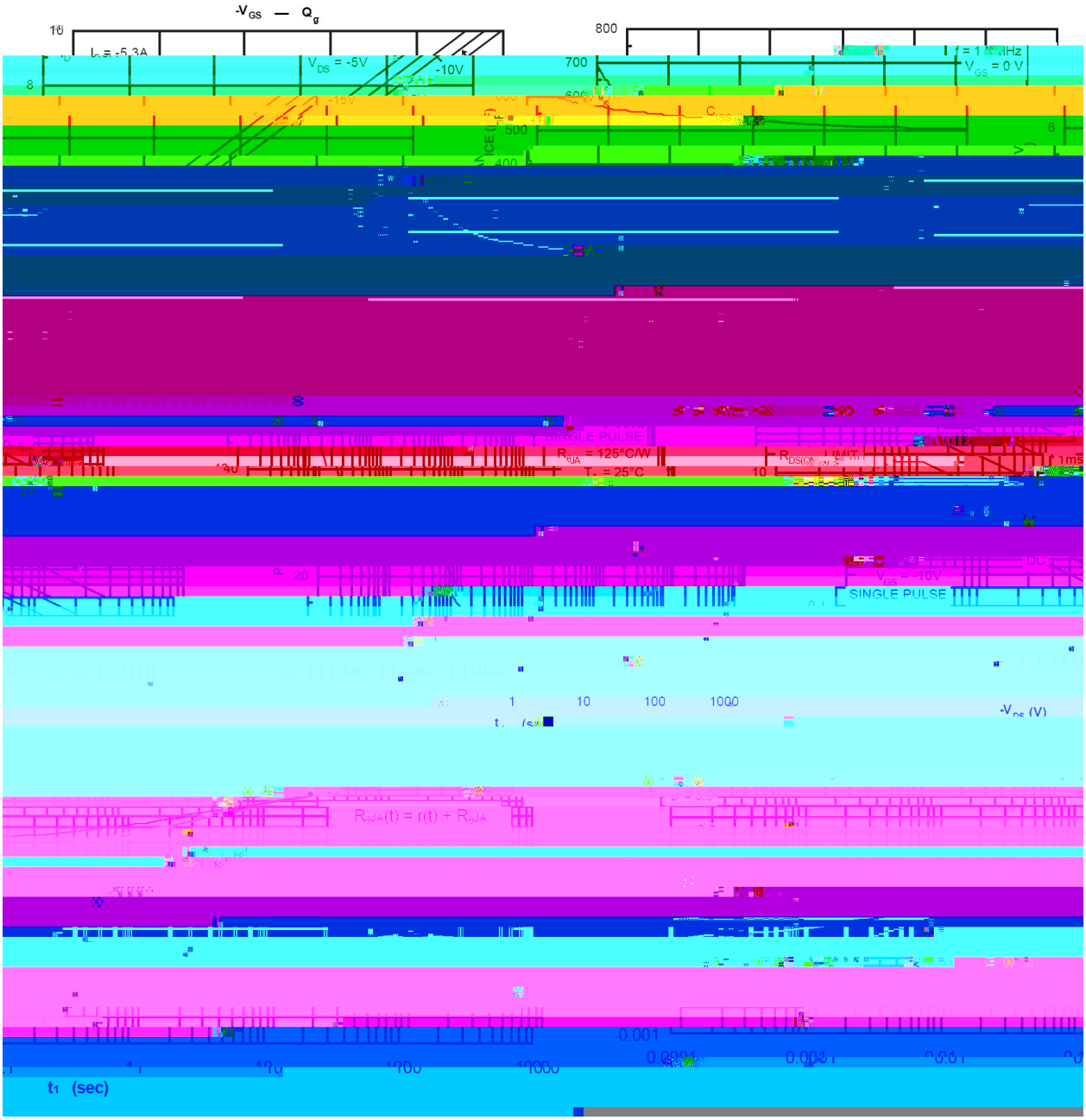
@ *f* Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Input Capacitance	C_{iss}	V_{DS}=–15V V_{GS}=0V f =1.0MHz		528		pF
Output Capacitance	C_{oss}			132		

Reverse Transfer Capacitcitis3
V

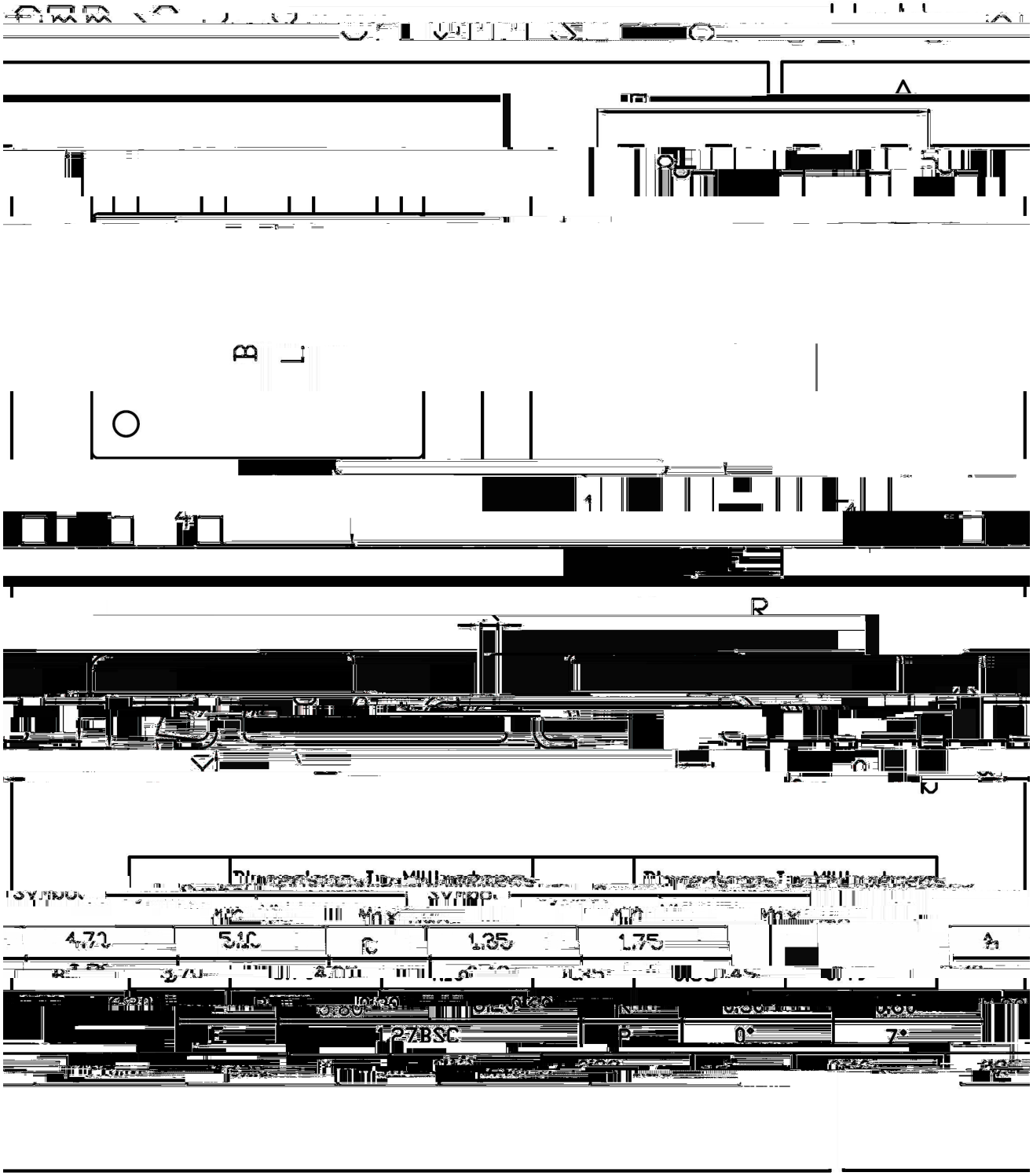
Ô ? d • Ž ¢


-I_D – -V_DS
30
V_GS=-10V
-6.0V
-5.0V
-4.5V
-4.0V
-3.5V
20
10
(A)
-I_D
R_DS(ON) – -I_D
2
1.8
V_GS=-4.0V
-4.5V
-5.0V
-6.0V
NORMALIZED
R_DS(ON)
1.4
1.2
0.8
0.2
25℃
3
0.01

Ô ? d • Ž ¢


-VGS — Qg
VDS = -5V
-10V
800
700
f = 1 MHz
VGS = 0 V
SINGLE PULSE
RθJA = 125°C/W
TA = 25°C
1mS
VGS = -10V
SINGLE PULSE
-VDS (V)
RθJA(t) = r(t) + RθJA
t1 (sec)

Ø ¤ =) ¢

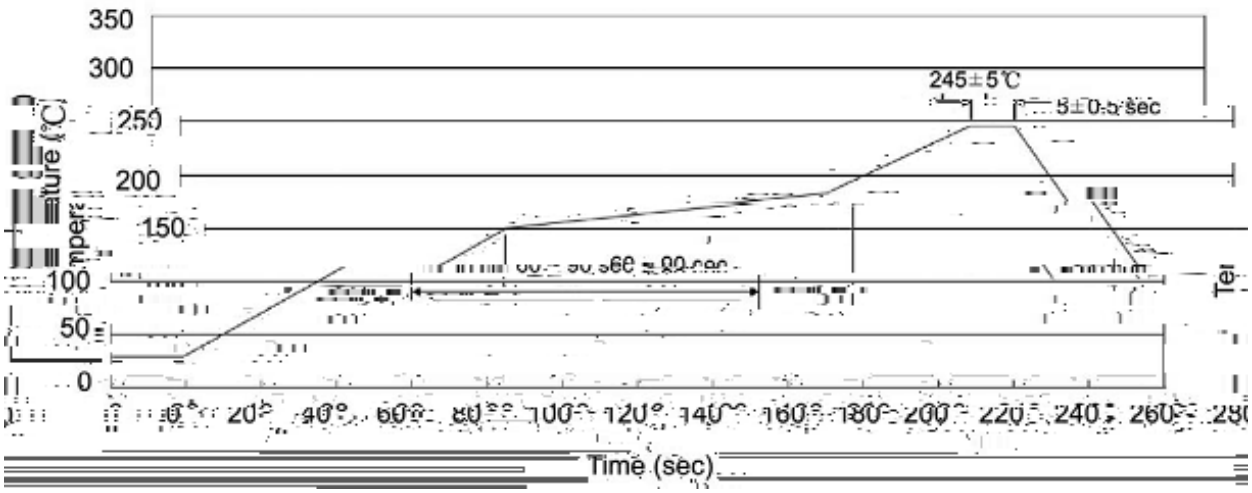


, M y *f*

ª ¢ y

BR • Á! b•Q G% eq•C%u•†d ¸ [Wñ• Å’ Breq• qC·)Uÿúñ‘° a•) X•) €Aà[U E• ‘P7• 0ðððð b•) w™

š WD t … • Ž ¢ x / :K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6



ª ¢ y Note:

1o• Ä ½ “ † 150 ½180-30Ž½